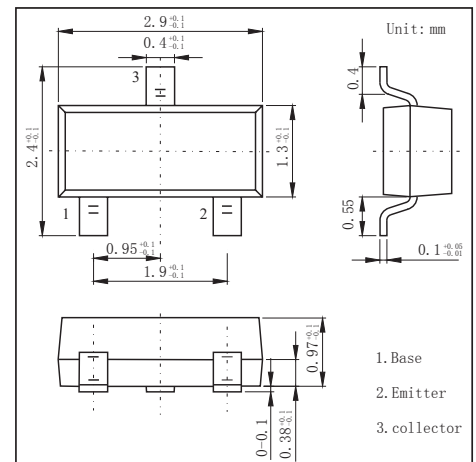


SOT-23-3 Plastic-Encapsulate Transistors
FEATURES

- Collector Current Capability $I_C=150\text{mA}$
- Collector Emitter Voltage $V_{CE0}=-50\text{V}$
- Compliments the 2SC2412
- PNP TRANSISTORS

MECHANICAL DATA

- Case style:SOT-23 -3molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-50	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	150	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -50 \mu\text{A}, I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -50 \mu\text{A}, I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -60 \text{ V}, I_E = 0$			-0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50 \text{ mA}, I_B = -5 \text{ mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50 \text{ mA}, I_B = -5 \text{ mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -6 \text{ V}, I_C = -1 \text{ mA}$	120		560	
Collector output capacitance	C_{ob}	$V_{CB} = -12 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4	5	pF
Transition frequency	f_T	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}, f = 30 \text{ MHz}$		140		MHz

RATINGS AND CHARACTERISTIC CURVES

